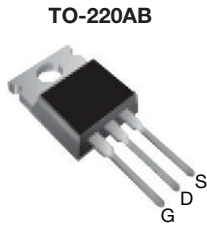


## E Series Power MOSFET



N-Channel MOSFET

### FEATURES

- Low figure-of-merit (FOM):  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Hard switched topologies
- Power factor correction power supplies (PFC)
- Switch mode power supplies (SMPS)
- Computing
  - PC silver box / ATX power supplies
- Lighting
  - Two stage LED lighting

PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	550
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V 0.145
$Q_g$ (Max.) (nC)	86
$Q_{gs}$ (nC)	14
$Q_{gd}$ (nC)	25
Configuration	Single

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and halogen-free	SiHP25N50E-BE3 <sup>a</sup>
	SiHP25N50E-GE3

#### Note


a. "-BE3" denotes alternate manufacturing location

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	500	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current <sup>a</sup>	$I_{DM}$	50	
Linear derating factor		0.2	W/°C
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	273	mJ
Maximum power dissipation	$P_D$	250	W
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Drain-source voltage slope	$dV/dt$	$T_J = 125$ °C	V/ns
Reverse diode $dV/dt$ <sup>d</sup>		25	
Soldering recommendations (peak temperature) <sup>c</sup>	For 10 s	300	°C

#### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature  
 b.  $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 4.4$  A  
 c. 1.6 mm from case  
 d.  $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C

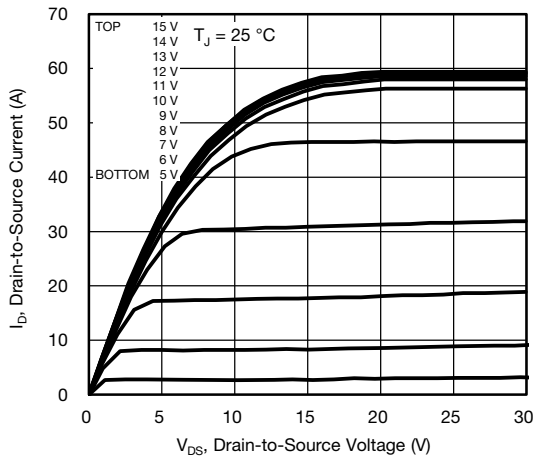
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.5	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	500	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.59	-	V/°C
Gate-source threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 1$	$\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	25	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 12\text{ A}$	-	0.125	0.145	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 12\text{ A}$	-	6.6	-	S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	1980	-	pF
Output capacitance	$C_{oss}$		-	105	-	
Reverse transfer capacitance	$C_{rss}$		-	8	-	
Effective output capacitance, energy related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	105	-	
Effective output capacitance, time related <sup>b</sup>	$C_{o(tr)}$		-	285	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 12\text{ A}, V_{DS} = 400\text{ V}$	-	57	86	nC
Gate-source charge	$Q_{gs}$		-	14	-	
Gate-drain charge	$Q_{gd}$		-	25	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 12\text{ A}, R_g = 9.1\text{ }\Omega, V_{GS} = 10\text{ V}$	-	19	38	ns
Rise time	$t_r$		-	36	72	
Turn-off delay time	$t_{d(off)}$		-	57	86	
Fall time	$t_f$		-	29	58	
Gate input resistance	$R_g$		$f = 1\text{ MHz}, \text{open drain}$	-	0.56	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	12	A
Pulsed diode forward current	$I_{SM}$		-	-	50	
Diode forward voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 16.5\text{ A}, V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$	-	338	-	ns
Reverse recovery charge	$Q_{rr}$		-	5.3	-	$\mu\text{C}$
Reverse recovery current	$I_{RRM}$		-	29	-	A

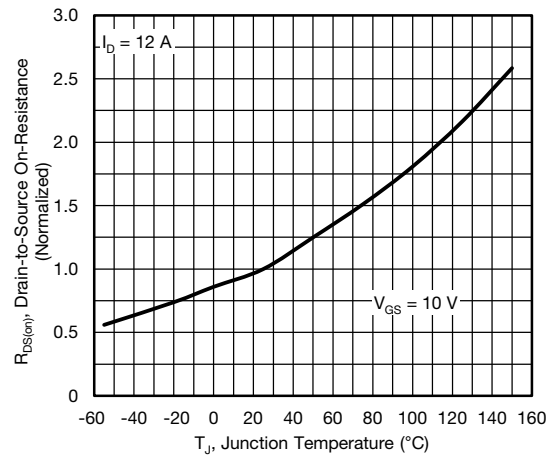
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

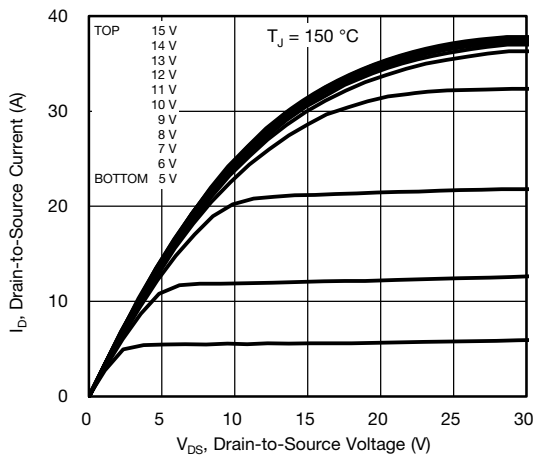
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



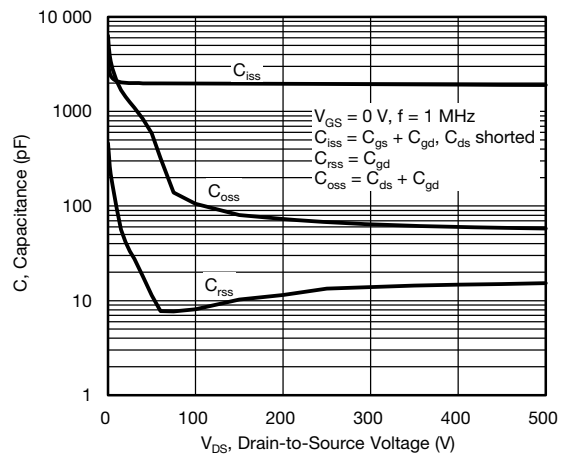
**Fig. 1 - Typical Output Characteristics**



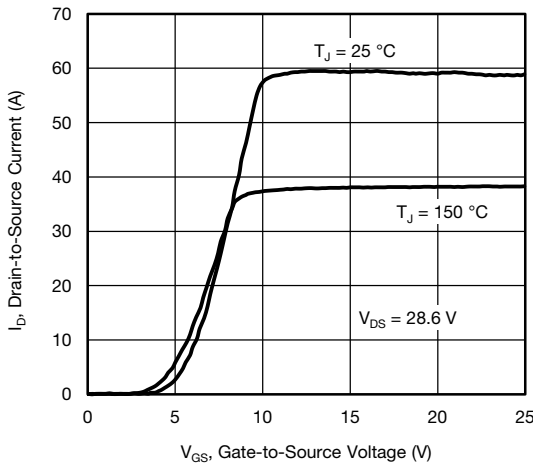
**Fig. 4 - Normalized On-Resistance vs. Temperature**



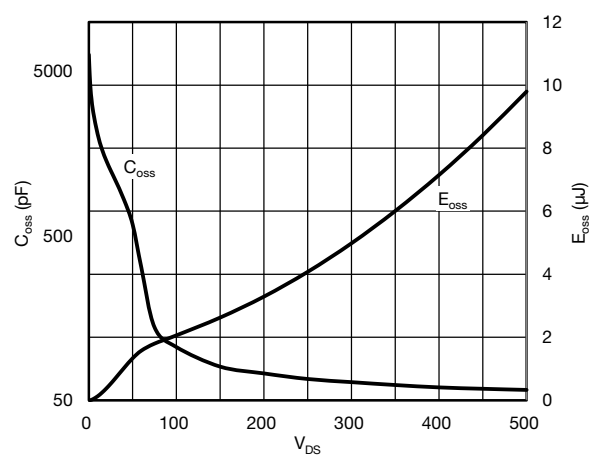
**Fig. 2 - Typical Output Characteristics**



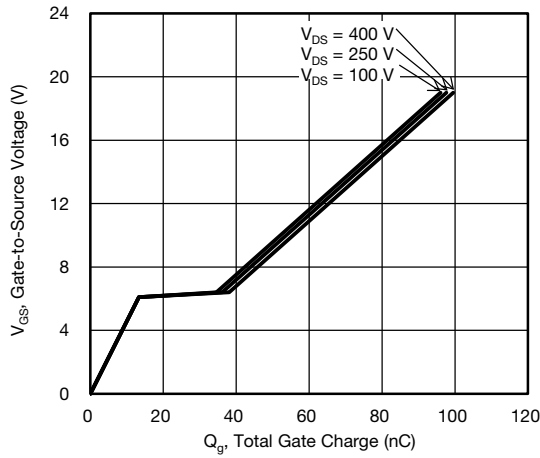
**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



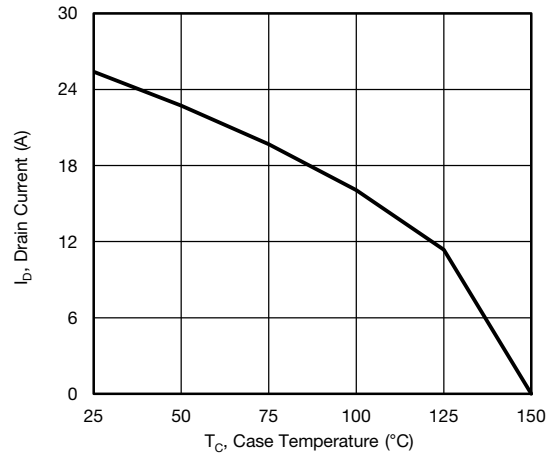
**Fig. 3 - Typical Transfer Characteristics**



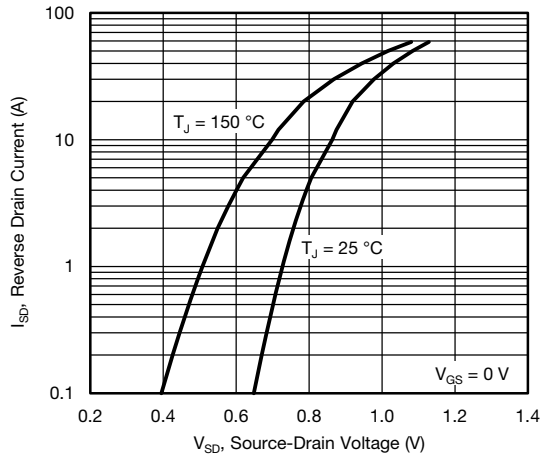
**Fig. 6 - Coss and Eoss vs. VDS**



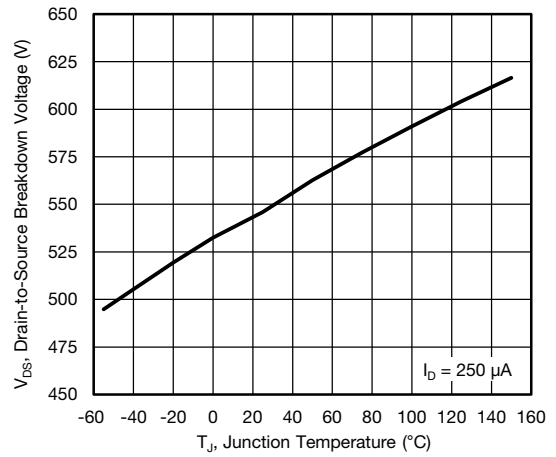
**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**



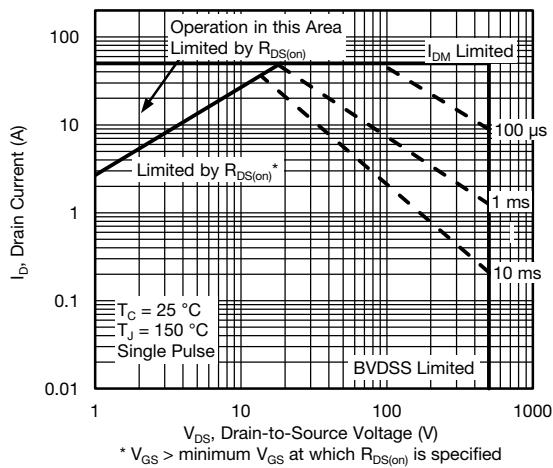
**Fig. 10 - Maximum Drain Current vs. Case Temperature**



**Fig. 8 - Typical Source-Drain Diode Forward Voltage**



**Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature**



**Fig. 9 - Maximum Safe Operating Area**

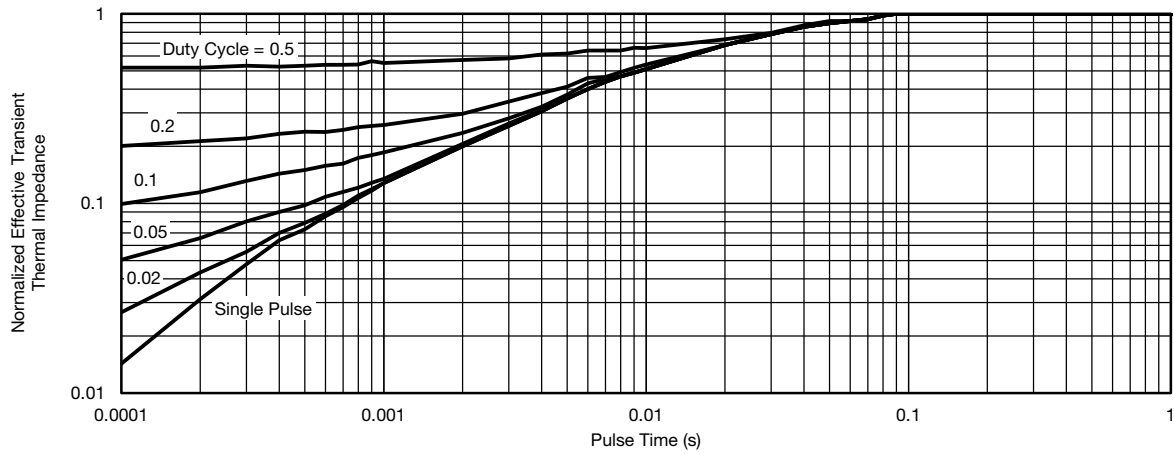


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

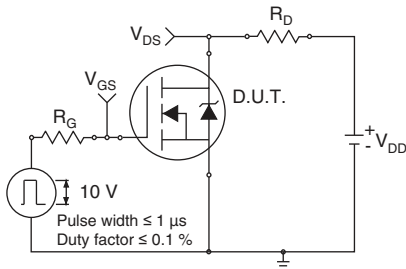


Fig. 13 - Switching Time Test Circuit

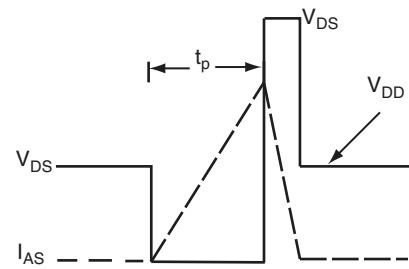


Fig. 16 - Unclamped Inductive Waveforms

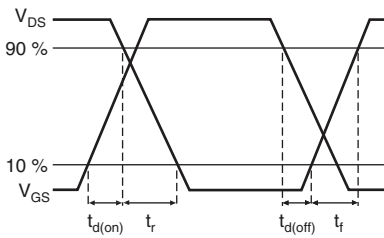


Fig. 14 - Switching Time Waveforms

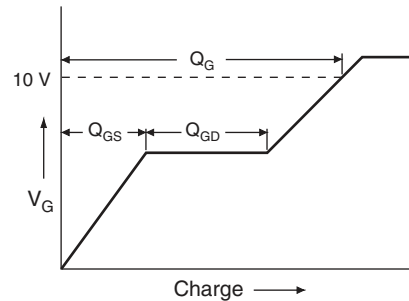


Fig. 17 - Basic Gate Charge Waveform

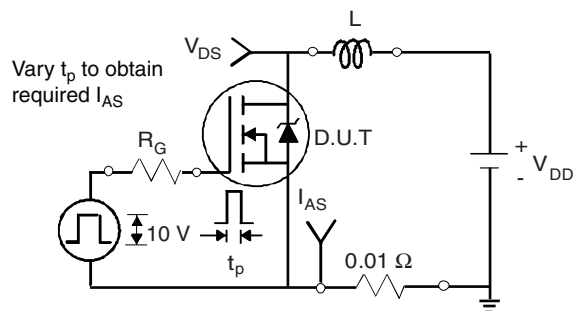


Fig. 15 - Unclamped Inductive Test Circuit

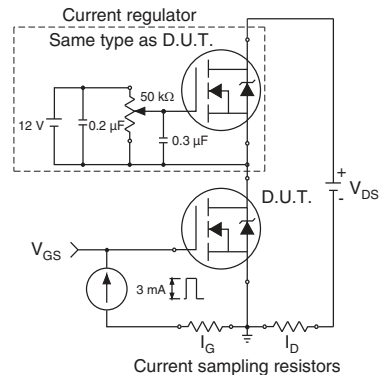
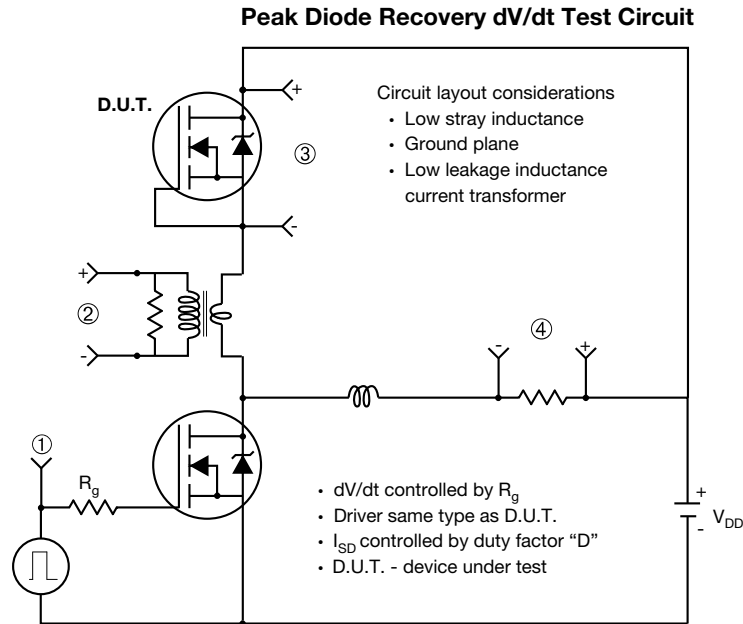


Fig. 18 - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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